



P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 30	0.0033 at $V_{GS} = - 10$ V	- 36	90 nC
	0.0046 at $V_{GS} = - 4.5$ V	- 29	

FEATURES

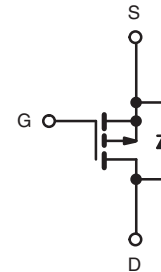
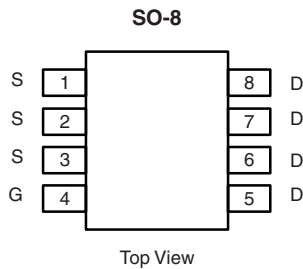
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Adaptor Switch
- High Current Load Switch
- Notebook



Ordering Information: Si4497DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	- 36	A
	$T_C = 70^\circ\text{C}$	- 29	
	$T_A = 25^\circ\text{C}$	- 24.8 ^{a, b}	
	$T_A = 70^\circ\text{C}$	- 19.2 ^{a, b}	
Pulsed Drain Current	I_{DM}	- 70	
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	- 6.5	
	$T_A = 25^\circ\text{C}$	- 2.9 ^{a, b}	
Avalanche Current	I_{AS}	- 30	mJ
Single-Pulse Avalanche Energy	E_{AS}	45	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	7.8	W
	$T_C = 70^\circ\text{C}$	5.0	
	$T_A = 25^\circ\text{C}$	3.5 ^{a, b}	
	$T_A = 70^\circ\text{C}$	2.2 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	29	35	$^\circ\text{C/W}$
Maximum Junction-to-Foot	R_{thJF}	13	16	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 80°C/W .
- Based on $T_C = 25^\circ\text{C}$.

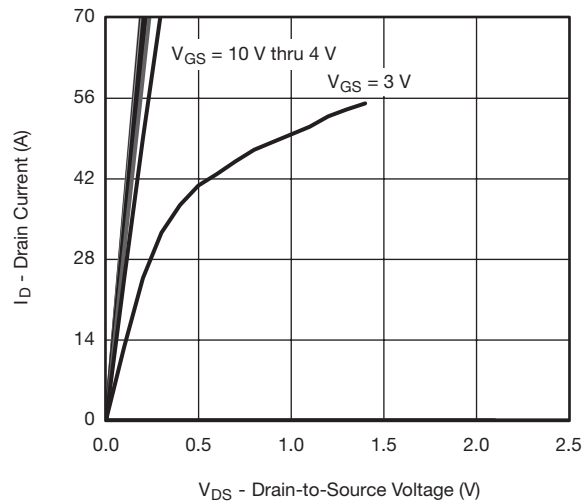
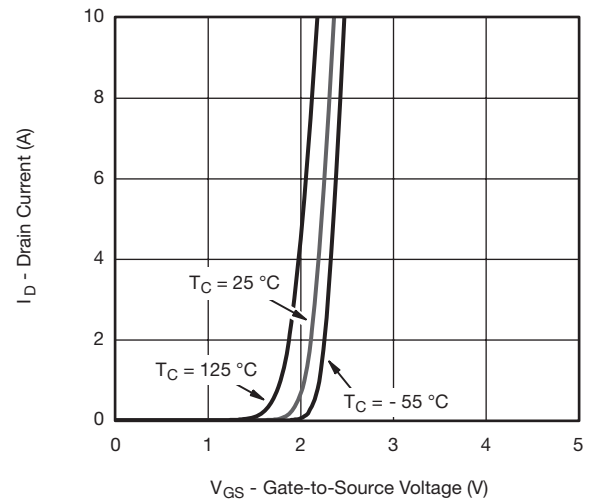
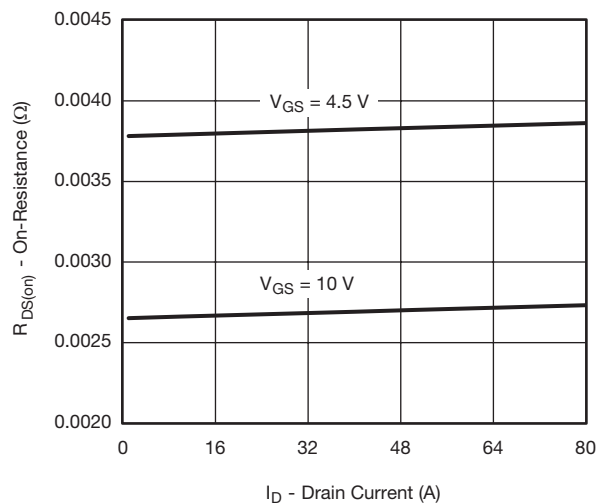
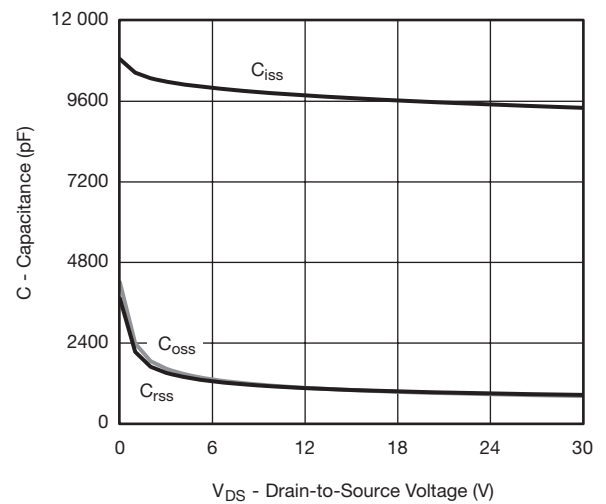
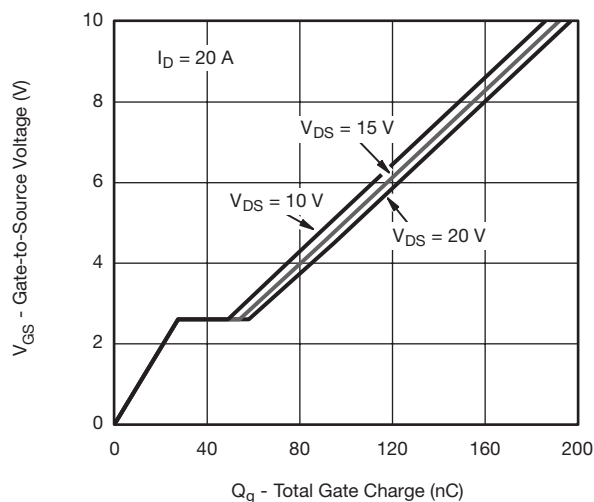
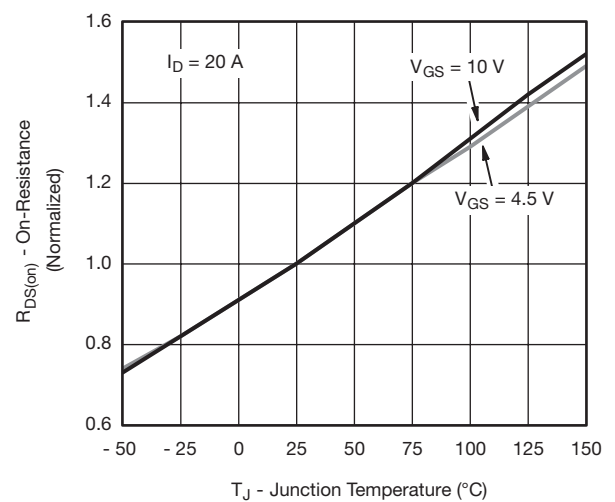
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 26		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 20 A		0.0027	0.0033	Ω
		V _{GS} = - 4.5 V, I _D = - 15 A		0.0038	0.0046	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 20 A		75		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		9685		pF
Output Capacitance	C _{oss}			995		
Reverse Transfer Capacitance	C _{rss}			995		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A		190	285	nC
		V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 20 A		90	135	
Gate-Source Charge	Q _{gs}			27.5		
Gate-Drain Charge	Q _{gd}			26.5		
Gate Resistance	R _g	f = 1 MHz	0.5	2.3	4.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		19	35	ns
Rise Time	t _r			13	25	
Turn-Off DelayTime	t _{d(off)}			115	200	
Fall Time	t _f			25	50	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		100	180	
Rise Time	t _r			75	150	
Turn-Off DelayTime	t _{d(off)}			100	180	
Fall Time	t _f			42	80	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 36	A
Pulse Diode Forward Current	I _{SM}				- 70	
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.70	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, dI/dt = 100 A/μs, T _J = 25 °C		31	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			23	45	nC
Reverse Recovery Fall Time	t _a			13		ns
Reverse Recovery Rise Time	t _b			18		

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

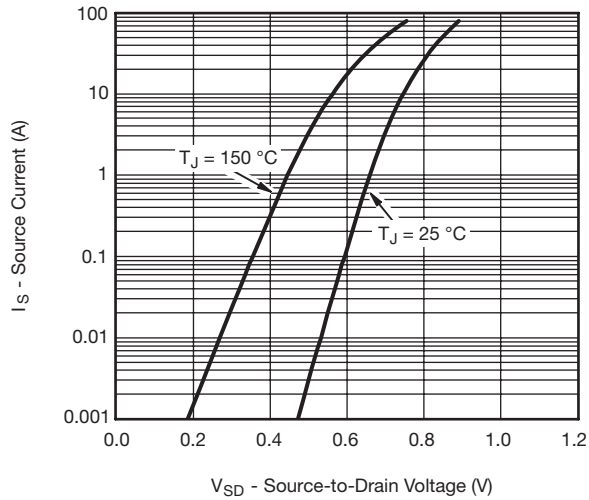
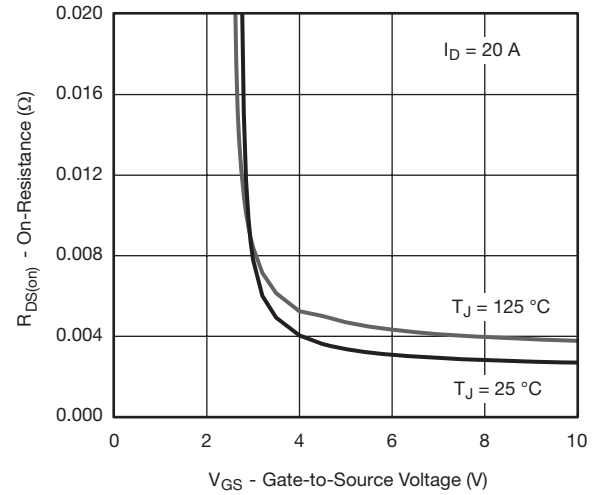
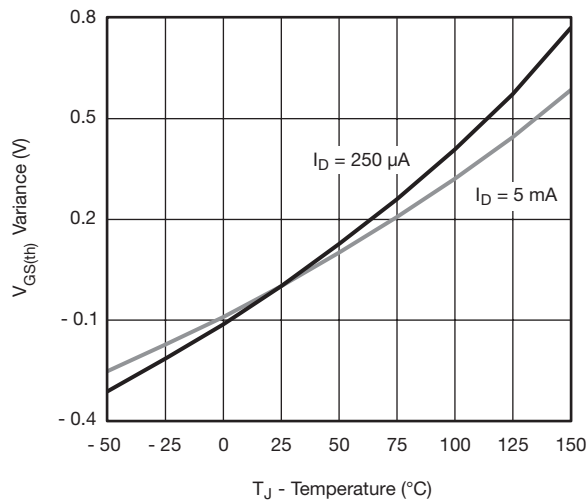
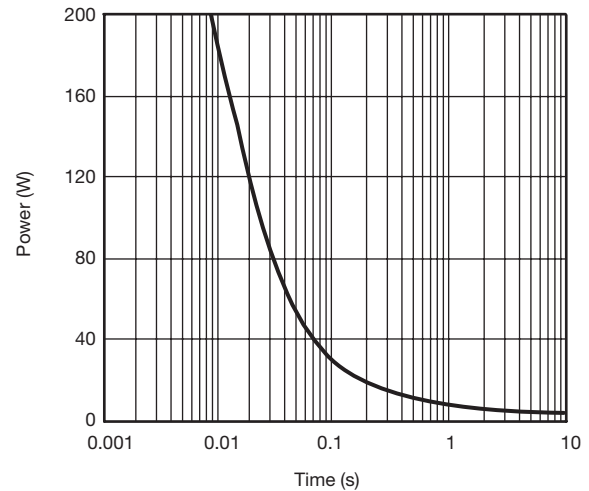
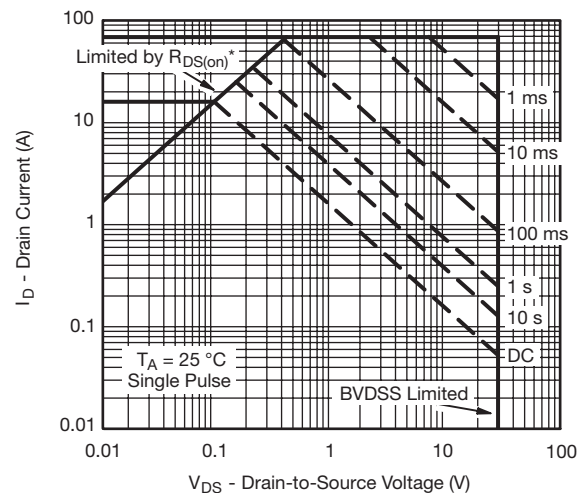
b. Guaranteed by design, not subject to production testing.

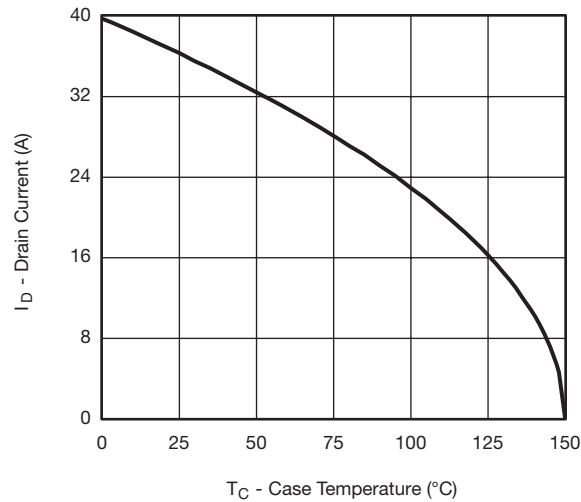
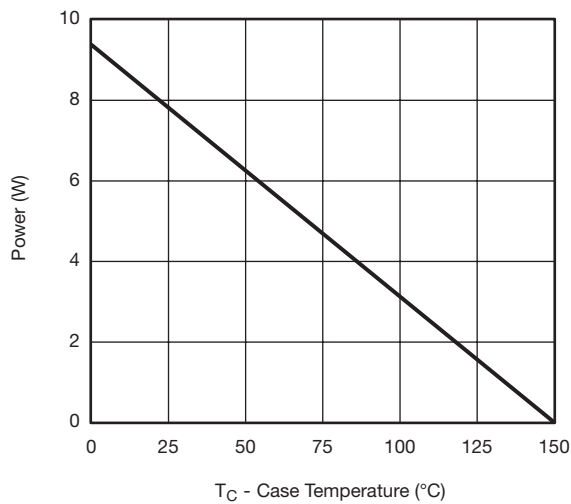
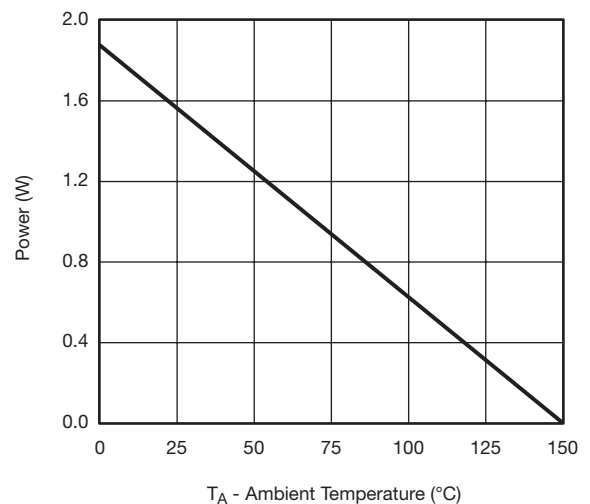
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Si4497DY

Vishay Siliconix

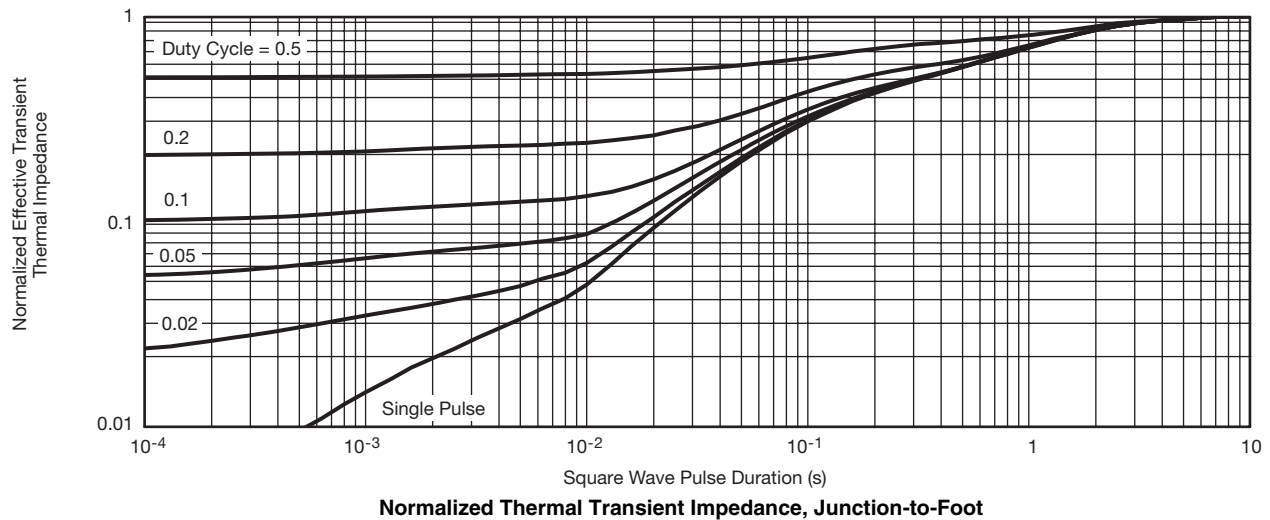
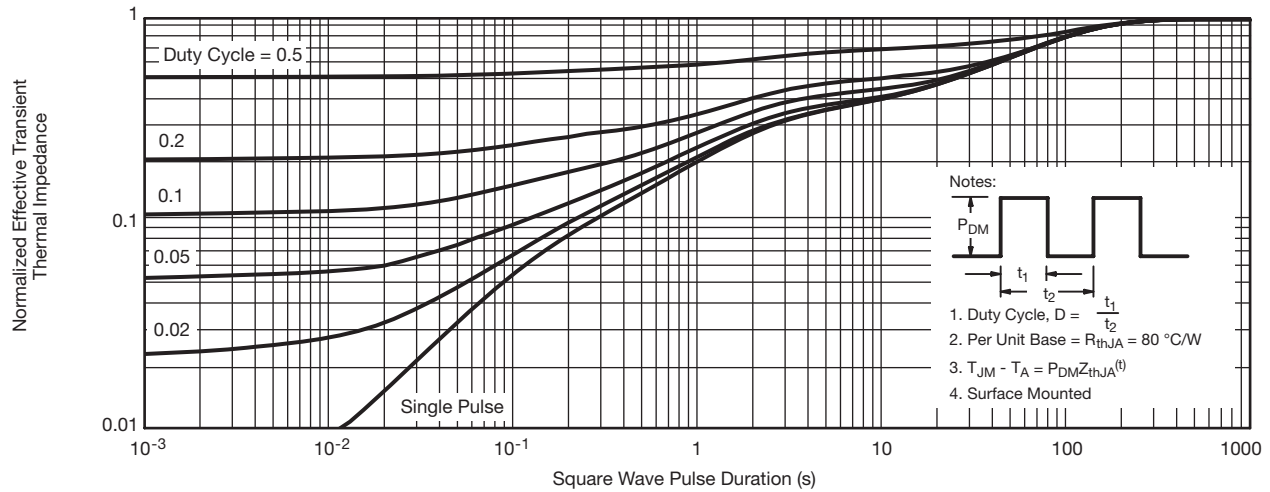
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Current Derating*

Power Derating, Junction-to-Foot

Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si4497DY

Vishay Siliconix

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65748.



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.